

TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2406

Power Amplifier Applications

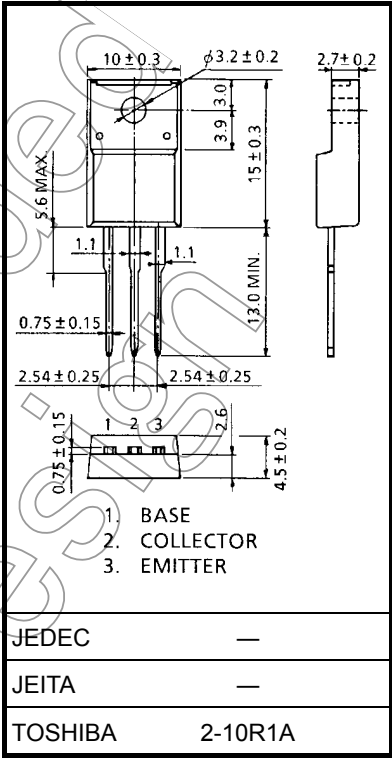
- High power dissipation: $P_C = 25\text{ W}$ ($T_c = 25^\circ\text{C}$)
- Good h_{FE} linearity

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	4	A
Base current	I_B	0.4	A
Collector power dissipation ($T_c = 25^\circ\text{C}$)	P_C	25	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



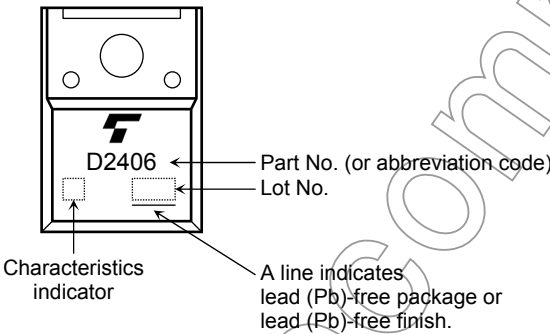
Weight: 1.7 g (typ.)

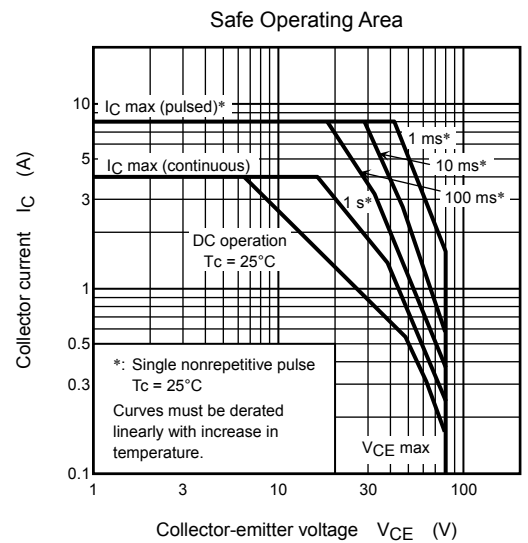
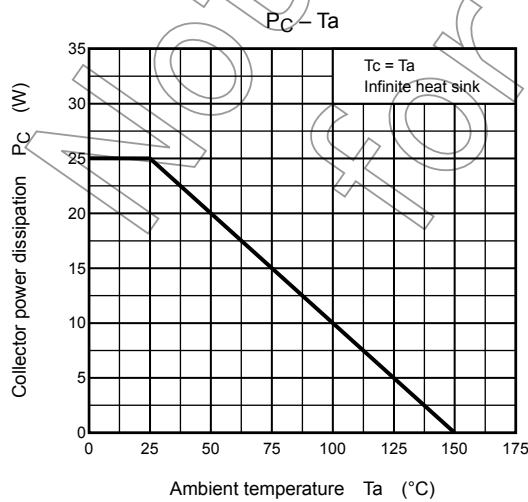
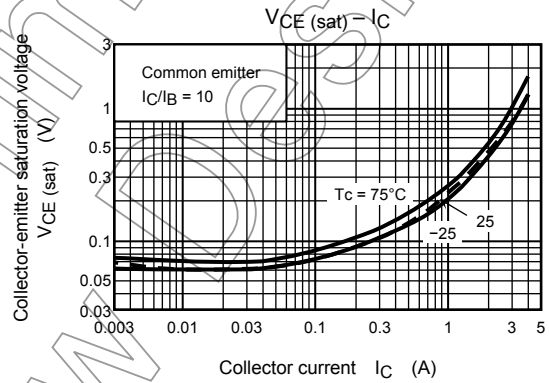
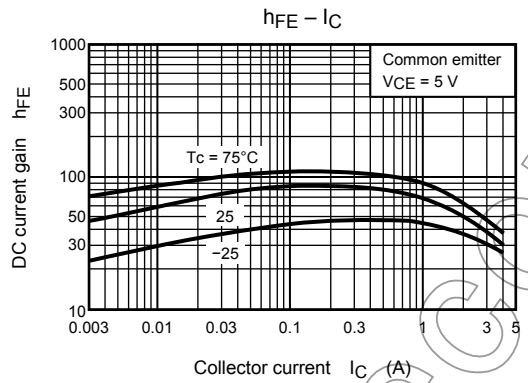
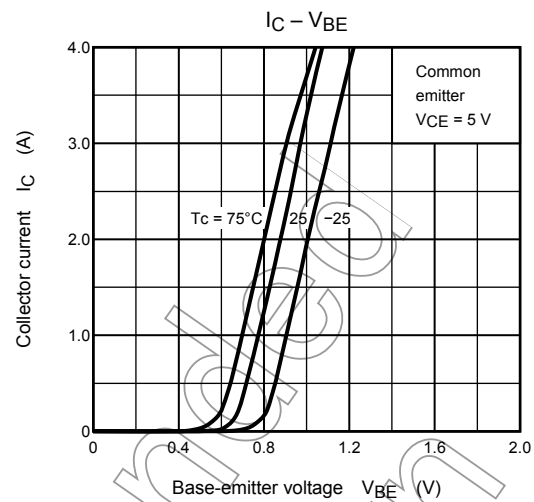
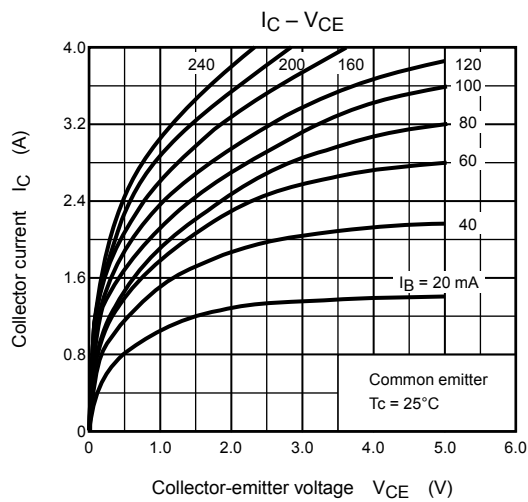
Electrical Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	ICBO	V _{CB} = 80 V, I _E = 0	—	—	30	μA
Emitter cut-off current	IEBO	V _{EB} = 5 V, I _C = 0	—	—	100	μA
Collector-emitter breakdown voltage	V _(BR) CEO	I _C = 50 mA, I _B = 0	80	—	—	V
Emitter-base breakdown voltage	V _(BR) EBO	I _E = 10 mA, I _C = 0	5	—	—	V
DC current gain	h _{FE} (1) (Note)	V _{CE} = 5 V, I _C = 0.5 A	70	—	240	
	h _{FE} (2)	V _{CE} = 5 V, I _C = 3 A	15	50	—	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 3 A, I _B = 0.3 A	—	0.45	1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 3 A	—	1.0	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 0.5 A	—	8.0	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	—	90	—	pF

Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

Marking





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